

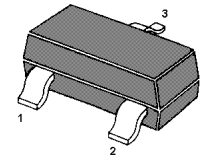
M8050 TRANSISTOR (NPN)

FEATURES

Complimentary to M8550

Collector Current: $I_C=0.8A$

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

MARKING: Y11

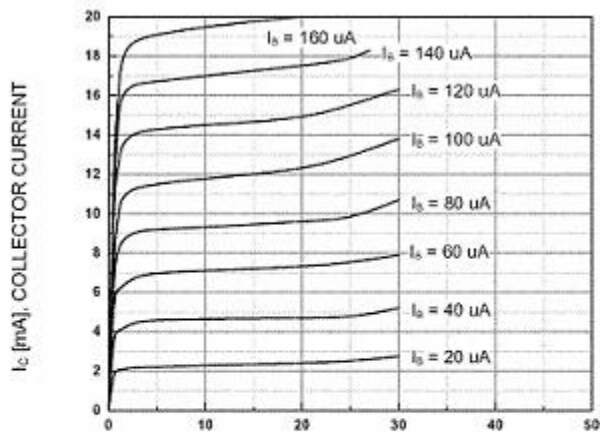
MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.8	A
P_C	Collector Dissipation	0.3	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

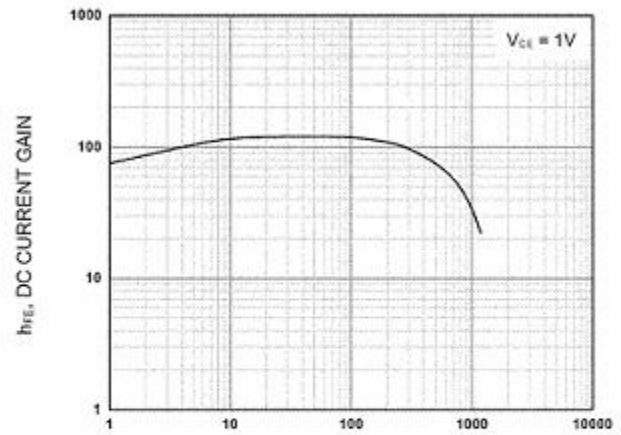
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB}=20V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$H_{FE(1)}$	$V_{CE}=1V, I_C=100mA$	200		350	
	$H_{FE(2)}$	$V_{CE}=1V, I_C=800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800mA, I_B=80mA$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800mA, I_B=80mA$			1.2	V
Transition frequency	f_T	$V_{CE}=6V, I_C=20mA$ $f=30MHz$	150			MHz

Typical Characteristics



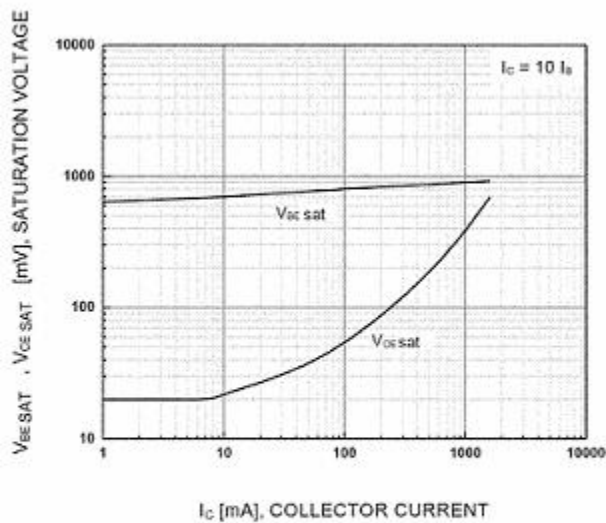
V_{CE} [V], COLLECTOR-EMITTER VOLTAGE

Static Characteristic

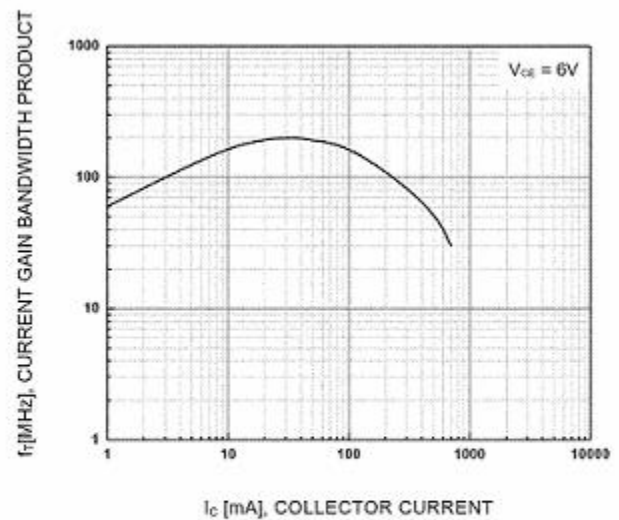


I_C [mA], COLLECTOR CURRENT

DC current Gain



**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**

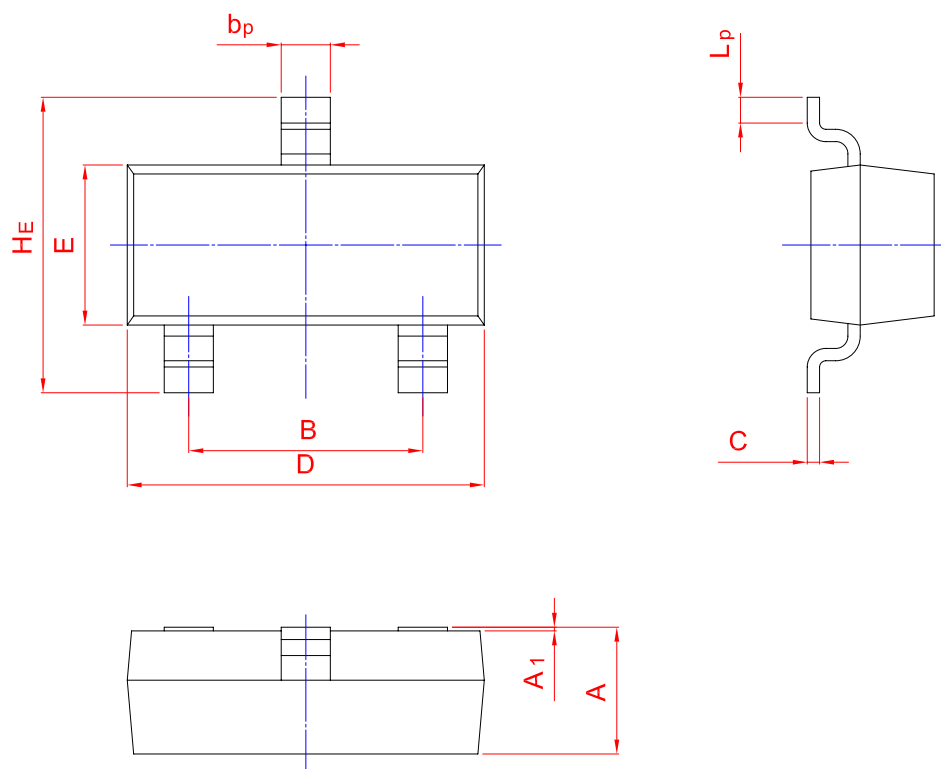


Current Gain Bandwidth Product

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20